400 Watt Peak Power Zener Transient Voltage Suppressors

Unidirectional

The SMA series is designed to protect voltage sensitive components from high voltage, high energy transients. They have excellent clamping capability, high surge capability, low zener impedance and fast response time. The SMA series is supplied in ON Semiconductor's exclusive, cost-effective, highly reliable SURMETIC[®] package and is ideally suited for use in communication systems, automotive, numerical controls, process controls, medical equipment, business machines, power supplies and many other industrial/consumer applications.

Features

- Working Peak Reverse Voltage Range 5.0 V to 78 V
- Standard Zener Breakdown Voltage Range 6.7 V to 91.25 V
- Peak Power 400 W @ 1 ms
- ESD Rating of Class 3 (> 16 kV) per Human Body Model
- Response Time is Typically < 1 ns
- Flat Handling Surface for Accurate Placement
- Package Design for Top Slide or Bottom Circuit Board Mounting
- Low Profile Package
- SZ Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC–Q101 Qualified and PPAP Capable
- Pb-Free Packages are Available*

Mechanical Characteristics:

CASE: Void-free, transfer-molded plastic

FINISH: All external surfaces are corrosion resistant and leads are readily solderable

MAXIMUM CASE TEMPERATURE FOR SOLDERING PURPOSES: 260°C for 10 Seconds

POLARITY: Cathode indicated by molded polarity notch or polarity band

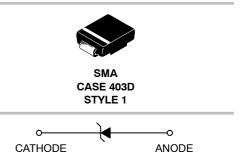
MOUNTING POSITION: Any



ON Semiconductor®

http://onsemi.com

PLASTIC SURFACE MOUNT ZENER OVERVOLTAGE TRANSIENT SUPPRESSORS 5.0 – 78 V, 400 W PEAK POWER



MARKING DIAGRAM



xx = Device Code (Refer to page 3)

A = Assembly Location

Y = Year

WW = Work Week

= Pb-Free Package

ORDERING INFORMATION

Device	Package	Shipping [†]
1SMAxxAT3G	SMA (Pb-Free)	5,000 / Tape & Reel
SZ1SMAxxAT3G	SMA (Pb-Free)	5,000 / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

DEVICE MARKING INFORMATION

*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

See specific marking information in the device marking column of the Electrical Characteristics table on page 3 of this data sheet.

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Peak Power Dissipation (Note 1) @ $T_L = 25^{\circ}C$, Pulse Width = 1 ms	P _{PK}	400	W
DC Power Dissipation @ T _L = 75°C Measured Zero Lead Length (Note 2) Derate Above 75°C Thermal Resistance from Junction to Lead	Ρ _D R _{θJL}	1.5 20 50	W mW/°C °C/W
DC Power Dissipation (Note 3) @ T _A = 25°C Derate Above 25°C Thermal Resistance from Junction to Ambient	Ρ _D R _{θJA}	0.5 4.0 250	W mW/°C °C/W
Forward Surge Current (Note 4) @ T _A = 25°C	I _{FSM}	40	A
Operating and Storage Temperature Range	T _J , T _{stg}	–65 to +150	°C

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

1. 10 X 1000 µs, non-repetitive.

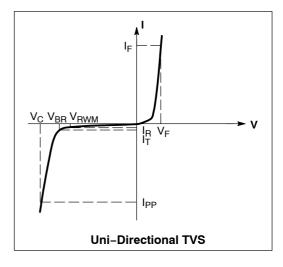
2. 1" square copper pad, FR-4 board.

3. FR-4 board, using ON Semiconductor minimum recommended footprint, as shown in 403B case outline dimensions spec.

4. 1/2 sine wave (or equivalent square wave), PW = 8.3 ms, duty cycle = 4 pulses per minute maximum.

Symbol	Parameter						
I _{PP}	Maximum Reverse Peak Pulse Current						
V _C	Clamping Voltage @ I _{PP}						
V _{RWM}	Working Peak Reverse Voltage						
I _R	Maximum Reverse Leakage Current @ V _{RWM}						
V _{BR}	Breakdown Voltage @ I _T						
Ι _Τ	Test Current						
١ _F	Forward Current						
V _F	Forward Voltage @ I _F						

ELECTRICAL CHARACTERISTICS (T_A = 25° C unless otherwise noted, V_F = 3.5 V Max. @ I_F = 30 A for all types) (Note 5)



5. 1/2 sine wave or equivalent, $\mathsf{PW}=8.3$ ms, non-repetitive duty cycle.

ELECTRICAL CHARACTERISTICS

		V		Breakdown Voltage			V _C @ I _{PP} (Note 8)		С Тур.	
	Device	V _{RWM} (Note 6)	I _R @ V _{RWM}	V _{BR} (Volts) (Note 7) @			@ I _T	Vc	I _{PP}	(Note 9)
Device*	Marking	Volts	μΑ	Min	Nom	Max	mA	Volts	Amps	pF
1SMA5.0AT3G	QE	5.0	400	6.4	6.7	7.0	10	9.2	43.5	2035
1SMA6.0AT3G	QG	6.0	400	6.67	7.02	7.37	10	10.3	38.8	1730
1SMA6.5AT3G	QK	6.5	250	7.22	7.6	7.98	10	11.2	35.7	1605
1SMA8.0AT3G	QR	8.0	25	8.89	9.36	9.83	1	13.6	29.4	1035
1SMA8.5AT3G	QT	8.5	5.0	9.44	9.92	10.4	1	14.4	27.8	1265
1SMA9.0AT3G	QV	9.0	2.5	10	10.55	11.1	1	15.4	26.0	1200
1SMA10AT3G	QX	10	2.5	11.1	11.7	12.3	1	17.0	23.5	1090
1SMA11AT3G	QZ	11	2.5	12.2	12.85	13.5	1	18.2	22.0	1000
1SMA12AT3G	RE	12	2.5	13.3	14.0	14.7	1	19.9	20.1	925
1SMA13AT3G	RG	13	2.5	14.4	15.15	15.9	1	21.5	18.6	860
1SMA14AT3G	RH	14	2.5	15.6	16.4	17.2	1	23.2	17.2	800
1SMA15AT3G	RM	15	2.5	16.7	17.6	18.5	1	24.4	16.4	758
1SMA16AT3G	RP	16	2.5	17.8	18.75	19.7	1	26.0	15.4	715
1SMA17AT3G	RR	17	2.5	18.9	19.9	20.9	1	27.6	14.5	680
1SMA18AT3G	RT	18	2.5	20	21.05	22.1	1	29.2	13.7	645
1SMA20AT3G	RV	20	2.5	22.2	23.35	24.5	1	32.4	12.3	585
1SMA22AT3G	RX	22	2.5	24.4	25.65	26.9	1	35.5	11.3	540
1SMA24AT3G	RZ	24	2.5	26.7	28.1	29.5	1	38.9	10.3	500
1SMA26AT3G	SE	26	2.5	28.9	30.4	31.9	1	42.1	9.5	460
1SMA28AT3G	SG	28	2.5	31.1	32.75	34.4	1	45.4	8.8	430
1SMA30AT3G	SK	30	2.5	33.3	35.05	36.8	1	48.4	8.3	405
1SMA33AT3G	SM	33	2.5	36.7	38.65	40.6	1	53.3	7.5	375
1SMA36AT3G	SP	36	2.5	40	42.1	44.2	1	58.1	6.9	345
1SMA40AT3G	SR	40	2.5	44.4	46.75	49.1	1	64.5	6.2	315
1SMA43AT3G	ST	43	2.5	47.8	50.3	52.8	1	69.4	5.8	295
1SMA45AT3G	SV	45	2.5	50	52.65	55.3	1	72.2	5.5	280
1SMA48AT3G	SX	48	2.5	53.3	56.1	58.9	1	77.4	5.2	265
1SMA54AT3G	TE	54	2.5	60	63.15	66.3	1	87.1	4.6	240
1SMA58AT3G	TG	58	2.5	64.4	67.8	71.5	1	93.6	4.3	225
1SMA70AT3G	TP	70	2.5	77.8	81.9	86.0	1	113	3.5	190
1SMA75AT3G	TR	75	2.5	83.3	87.7	92.1	1	121	3.3	180

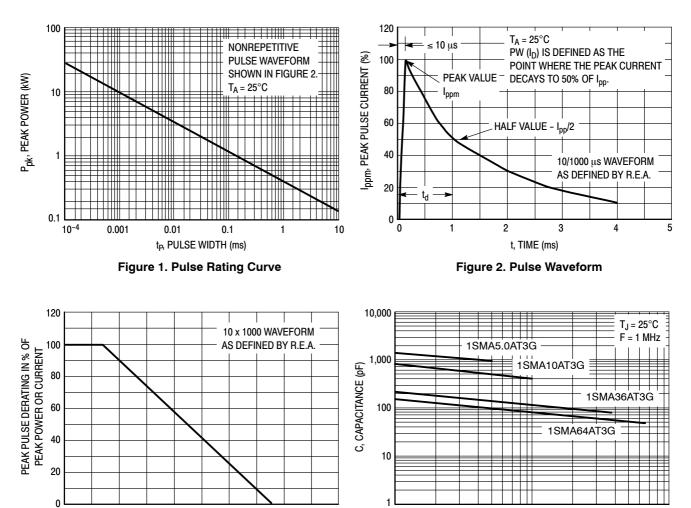
6. A transient suppressor is normally selected according to the working peak reverse voltage (V_{RWM}), which should be equal to or greater than the DC or continuous peak operating voltage level. 7. V_{BR} measured at pulse test current I_T at an ambient temperature of 25°C. 8. Surge current waveform per Figure 2 and derate per Figure 3.

9. Bias voltage = 0 V, F = 1.0 MHz, $T_J = 25^{\circ}C$.

†Please see 1SMA10CAT3 to 1SMA75CAT3 for Bidirectional devices.

* Include SZ-prefix devices where applicable.

RATING AND TYPICAL CHARACTERISTIC CURVES



80 120 160 200 T_A, AMBIENT TEMPERATURE (°C)

Figure 3. Pulse Derating Curve

40

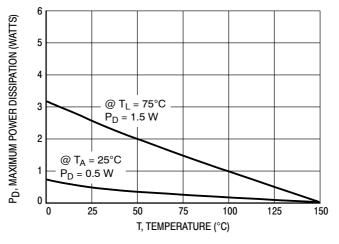
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Figure 4. Typical Junction Capacitance vs. Bias Voltage

10

BIAS VOLTAGE (VOLTS)

100

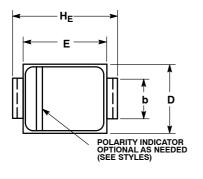


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Figure 5. Steady State Power Derating

PACKAGE DIMENSIONS

SMA CASE 403D-02 ISSUE F



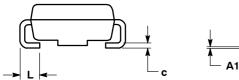
NOTES: 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982. 2. CONTROLLING DIMENSION: INCH.

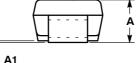
CONTROLLING DIMENSION: INCH.
403D-01 OBSOLETE, NEW STANDARD IS 403D-02.

	MILLIMETERS			INCHES				
DIM	MIN	NOM	MAX	MIN	NOM	MAX		
Α	1.97	2.10	2.20	0.078	0.083	0.087		
A1	0.05	0.10	0.15	0.002	0.004	0.006		
b	1.27	1.45	1.63	0.050	0.057	0.064		
С	0.15	0.28	0.41	0.006	0.011	0.016		
D	2.29	2.60	2.92	0.090	0.103	0.115		
Е	4.06	4.32	4.57	0.160	0.170	0.180		
HE	4.83	5.21	5.59	0.190	0.205	0.220		
L	0.76	1.14	1.52	0.030	0.045	0.060		

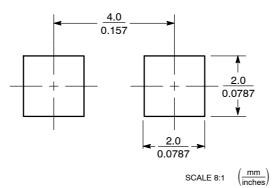
STYLE 1:

PIN 1. CATHODE (POLARITY BAND) 2. ANODE





SOLDERING FOOTPRINT*



*For additional information on our Pb–Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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